**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

### 3. Applications

- DC to DC conversion
- · Battery management
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter             | Conditions  |     | Min | Тур | Max  | Unit |
|---------------------|-----------------------|---|-----|-----|-----|------|------|
| $V_{DS}$            | drain-source voltage  | T <sub>j</sub> = 25 °C  |     | -   | -   | 25   | V    |
| $V_{GS}$            | gate-source voltage   |   |     | -20 | -   | 20   | V    |
| I <sub>D</sub>      | drain current         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s               | [1] | -   | -   | 22.3 | А    |
| Static charac       | cteristics            |   |     |     |     | ·    | ·    |
| R <sub>DSon</sub>   | drain-source on-state | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 13.1 A; T <sub>j</sub> = 25 °C |     | -   | 5.3 | 6.2  | mΩ   |
|                     | resistance            | $V_{GS}$ = 4.5 V; $I_D$ = 11.2 A; $T_j$ = 25 °C                         |     | -   | 6.8 | 8.5  | mΩ   |
| Dynamic cha         | aracteristics         |   |     |     |     | ·    |      |
| Q <sub>G(tot)</sub> | total gate charge     | $V_{DS}$ = 12.5 V; $I_{D}$ = 11.2 A; $V_{GS}$ = 4.5 V; $T_{j}$ = 25 °C  |     | -   | 8.1 | 12.2 | nC   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



25 V, N-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline  | Graphic symbol |
|-----|--------|-------------|---------------------|----------------|
| 1   | S      | source      | 1 2 3 4             | D              |
| 2   | S      | source      |                     |                |
| 3   | S      | source      |                     | G—(FA)         |
| 4   | G      | gate        | l h d               | mbb076 S       |
| 5   | D      | drain       |                     |                |
| 6   | D      | drain       |                     |                |
| 7   | D      | drain       | MLPAK33 (SOT8002-1) |                |
| 8   | D      | drain       |                     |                |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number | Package |   |           |  |  |  |  |  |
|-------------|---------|---|-----------|--|--|--|--|--|
|             | Name    | Description   | Version   |  |  |  |  |  |
| PXN6R2-25QL |         | plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body | SOT8002-1 |  |  |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PXN6R2-25QL | 9AG          |

25 V, N-channel Trench MOSFET

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter  | Conditions  |     | Min | Max  | Unit |
|----------------------|--|---|-----|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                             | T <sub>j</sub> = 25 °C  |     | -   | 25   | V    |
| V <sub>GS</sub>      | gate-source voltage                              |   |     | -20 | 20   | V    |
| I <sub>D</sub>       | drain current                                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s                         | [1] | -   | 22.3 | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                                  | [1] | -   | 13.1 | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C                                 | [1] | -   | 8.3  | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C                                   |     | -   | 65   | Α    |
| I <sub>DM</sub>      | peak drain current                               | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                               |     | -   | 90   | Α    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>amb</sub> = 25 °C; t ≤ 5 s   | [1] | -   | 4.8  | W    |
|                      |  | T <sub>amb</sub> = 25 °C  | [1] | -   | 1.7  | W    |
|                      |  | T <sub>sp</sub> = 25 °C   |     | -   | 40.3 | W    |
| T <sub>j</sub>       | junction temperature                             |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>     | ambient temperature                              |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>     | storage temperature                              |   |     | -65 | 150  | °C   |
| Source-draiı         | n diode  |   |     | 1   |      |      |
| I <sub>S</sub>       | source current                                   | T <sub>amb</sub> = 25 °C  | [1] | -   | 1.5  | Α    |
| Avalanche r          | uggedness  |   | 1   | 1   | -    |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 2.4 A; DUT in valanche (unclamped) |     | -   | 30   | mJ   |
|                      | •  |   |     |     |      |      |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

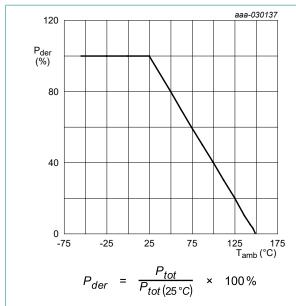


Fig. 1. Normalized total power dissipation as a function of ambient temperature

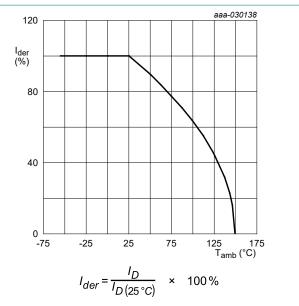


Fig. 2. Normalized continous drain current as a function of ambient temperature

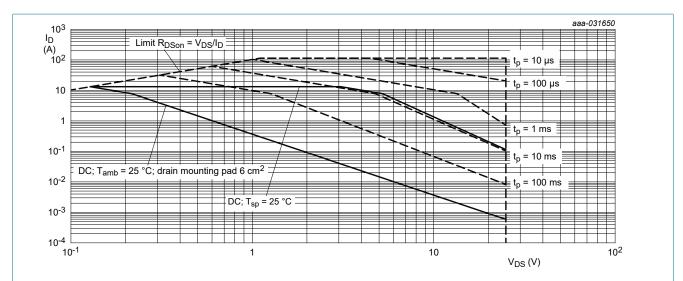


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

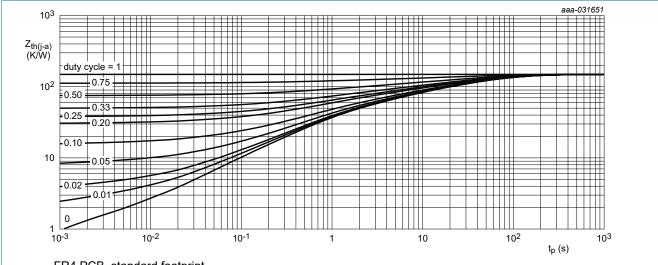
25 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

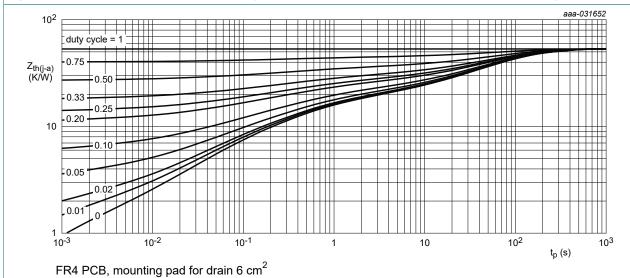
| Symbol                | Parameter  | Conditions           |     | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from                          | in free air          | [1] | -   | 150 | 190 | K/W  |
|                       | junction to ambient                              |                      | [2] | -   | 60  | 75  | K/W  |
|                       |  | in free air; t ≤ 5 s | [2] | -   | 21  | 26  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |                      |     | -   | 2.1 | 3.1 | K/W  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

25 V, N-channel Trench MOSFET

# 10. Characteristics

#### Table 7. Characteristics

| Symbol                 | Parameter                             | Conditions  | Min | Тур  | Max  | Unit |
|------------------------|---------------------------------------|---|-----|------|------|------|
| Static chara           | acteristics                           |   |     |      |      |      |
| V <sub>(BR)DSS</sub>   | drain-source<br>breakdown voltage     | $I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C                          | 25  | -    | -    | V    |
| $V_{GSth}$             | gate-source threshold voltage         | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                     | 1.2 | 1.7  | 2.2  | V    |
| I <sub>DSS</sub>       | drain leakage current                 | V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -   | -    | 1    | μΑ   |
| I <sub>GSS</sub>       | gate leakage current                  | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -   | -    | 100  | nA   |
|                        |                                       | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -   | -    | -100 | nA   |
| R <sub>DSon</sub>      | drain-source on-state                 | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 13.1 A; T <sub>j</sub> = 25 °C     | -   | 5.3  | 6.2  | mΩ   |
|                        | resistance                            | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 13.1 A; T <sub>j</sub> = 150 °C    | -   | 8.2  | 9.7  | mΩ   |
|                        |                                       | $V_{GS} = 4.5 \text{ V}; I_D = 11.2 \text{ A}; T_j = 25 \text{ °C}$         | -   | 6.8  | 8.5  | mΩ   |
| 9fs                    | forward transconductance              | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 13.1 A; T <sub>j</sub> = 25 °C     | -   | 32   | -    | S    |
| R <sub>G</sub>         | gate resistance                       | f = 1 MHz   | -   | 11.5 | -    | Ω    |
| Dynamic ch             | naracteristics                        |   | ,   |      | '    |      |
| Q <sub>G(tot)</sub>    | total gate charge                     | $V_{DS}$ = 12.5 V; $I_{D}$ = 13.1 A; $V_{GS}$ = 10 V; $I_{j}$ = 25 °C       | -   | 17   | 25.5 | nC   |
|                        |                                       | V <sub>DS</sub> = 12.5 V; I <sub>D</sub> = 11.2 A; V <sub>GS</sub> = 4.5 V; | -   | 8.1  | 12.2 | nC   |
| Q <sub>GS</sub>        | gate-source charge                    | T <sub>j</sub> = 25 °C  | -   | 3.2  | -    | nC   |
| Q <sub>GS(th)</sub>    | pre-threshold gate-<br>source charge  |   | -   | 2    | -    | nC   |
| Q <sub>GS(th-pl)</sub> | post-threshold gate-<br>source charge |   | -   | 1.2  | -    | nC   |
| Q <sub>GD</sub>        | gate-drain charge                     |   | -   | 2.2  | -    | nC   |
| $V_{GSpl}$             | gate-source plateau<br>voltage        | V <sub>DS</sub> = 12.5 V; I <sub>D</sub> = 11.2 A; T <sub>j</sub> = 25 °C   | -   | 2.8  | -    | V    |
| C <sub>iss</sub>       | input capacitance                     | V <sub>DS</sub> = 12.5 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                 | -   | 1200 | -    | pF   |
| C <sub>oss</sub>       | output capacitance                    | T <sub>j</sub> = 25 °C  | -   | 430  | -    | pF   |
| C <sub>rss</sub>       | reverse transfer capacitance          |   | -   | 76   | -    | pF   |
| t <sub>d(on)</sub>     | turn-on delay time                    | V <sub>DS</sub> = 12.5 V; I <sub>D</sub> = 11.2 A; V <sub>GS</sub> = 4.5 V; | -   | 5    | -    | ns   |
| t <sub>r</sub>         | rise time                             | $R_{G(ext)} = 5 \Omega; T_j = 25 °C$  | -   | 8    | -    | ns   |
| $t_{d(off)}$           | turn-off delay time                   | 1   | -   | 6    | -    | ns   |
| t <sub>f</sub>         | fall time                             |   | -   | 3    | -    | ns   |
| Source-dra             | in diode                              |   |     |      |      |      |
| V <sub>SD</sub>        | source-drain voltage                  | I <sub>S</sub> = 1.5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -   | 0.7  | 1.2  | V    |
| t <sub>rr</sub>        | reverse recovery time                 | $I_S = 1.5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$                | -   | 15   | -    | ns   |
| Q <sub>r</sub>         | recovered charge                      | $V_{GS} = 4.5 \text{ V}; V_{DS} = 12.5 \text{ V}; T_j = 25 \text{ °C}$      | -   | 6    | -    | nC   |
| t <sub>a</sub>         | reverse recovery rise time            |   | -   | 8    | -    | ns   |
| t <sub>b</sub>         | reverse recovery fall time            |   | -   | 7    | -    | ns   |

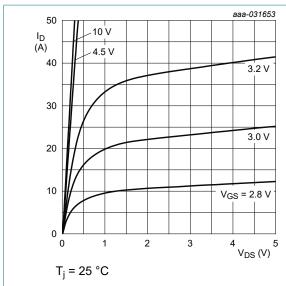


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

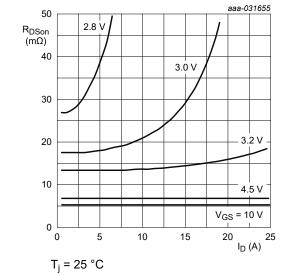


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

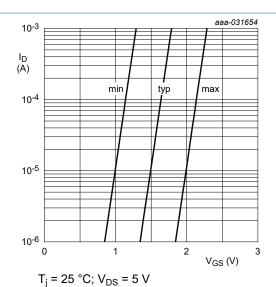


Fig. 7. Subthreshold drain current as a function of gate-source voltage

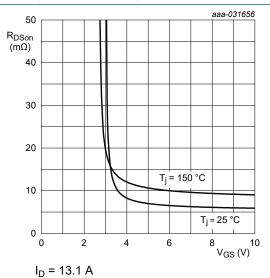


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

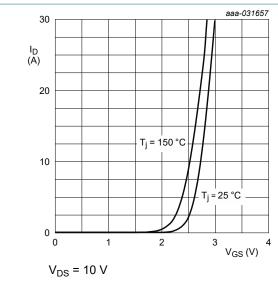


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

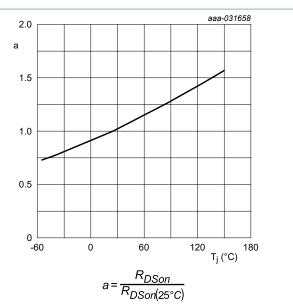


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

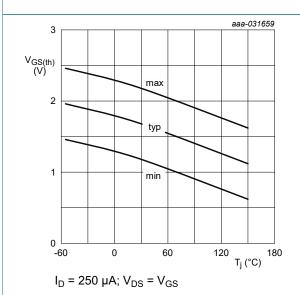
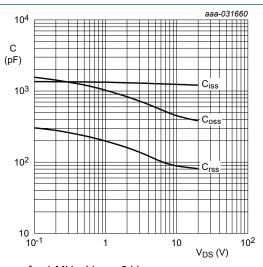


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

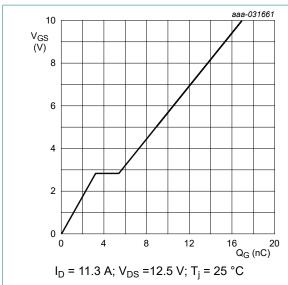


Fig. 14. Gate-source voltage as a function of gate charge; typical values

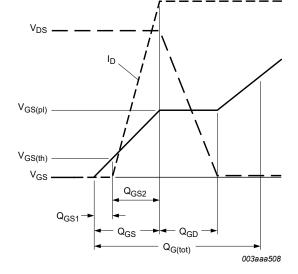


Fig. 15. Gate charge waveform definitions

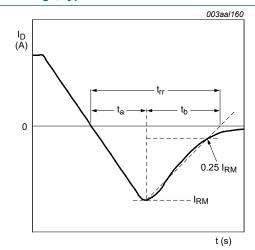


Fig. 16. Reverse recovery timing definition

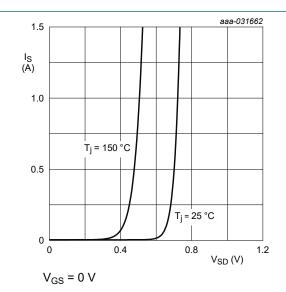
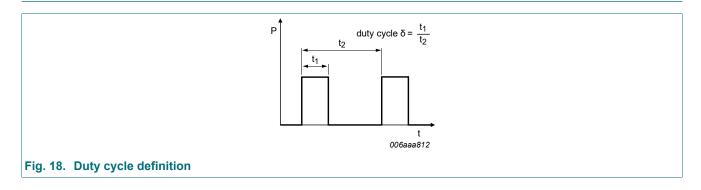


Fig. 17. Source current as a function of source-drain voltage; typical values

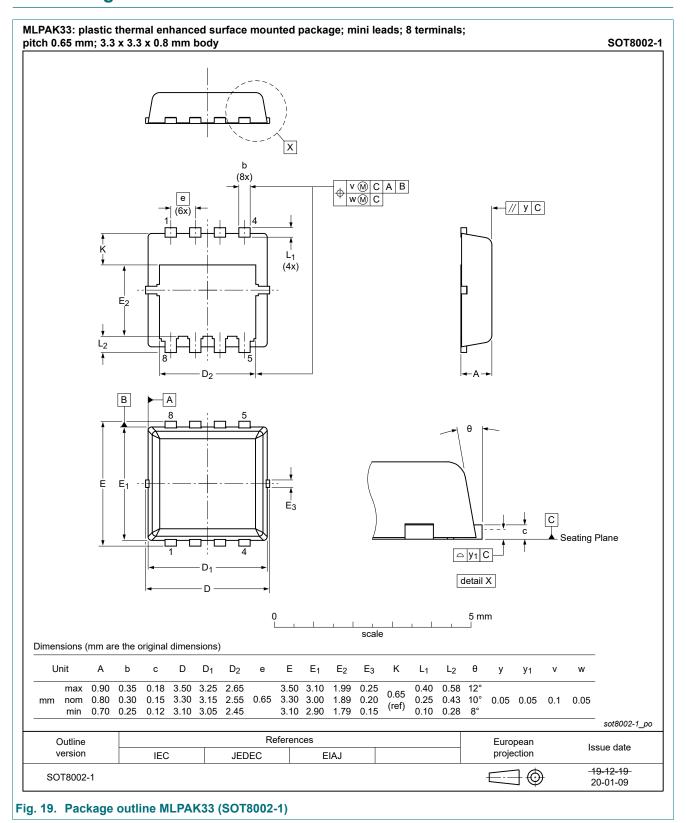
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# 11. Test information



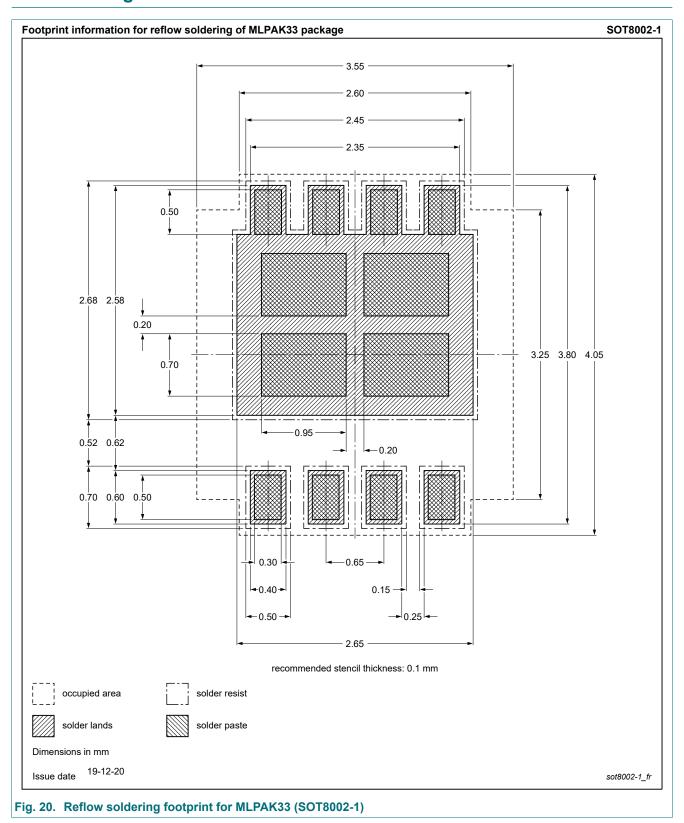
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID   | Release date | Data sheet status  | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PXN6R2-25QL v.1 | 20201102     | Product data sheet | -             | -          |

#### 25 V, N-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
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- Please consult the most recently issued document before initiating or completing a design.
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### 25 V, N-channel Trench MOSFET

### **Contents**

| 1.  | General description     | 1  |
|-----|-------------------------|----|
| 2.  | Features and benefits   | 1  |
| 3.  | Applications            | 1  |
| 4.  | Quick reference data    | 1  |
| 5.  | Pinning information     | 2  |
| 6.  | Ordering information    | 2  |
| 7.  | Marking                 | 2  |
| 8.  | Limiting values         | 3  |
| 9.  | Thermal characteristics | 5  |
| 10  | . Characteristics       | 6  |
| 11. | . Test information      | 10 |
| 12  | . Package outline       | 11 |
|     | . Soldering             |    |
|     | . Revision history      |    |
|     | . Legal information     |    |
|     |                         |    |

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